

# **MARKED UP VERSION OF REPLACED SECTION OF THE SPECIFICATION**

Pages 76 and 77, "Abstract of the Disclosure" section,  
the marked up version of this section is:

[A semiconductor device comprising] A semiconductor chip  
[having] has a quadrangle main surface, a wiring substrate  
[with the semiconductor chip disposed on a main surface  
thereof], and a resin seal member for sealing the  
semiconductor chip, in which the resin seal member [having]  
has a quadrangle main surface which confronts the main surface  
of the semiconductor chip[,]. [and a] A gate cut trace portion  
is formed on a side face extending along a first side of the  
main surface of the resin seal member. [wherein the first side  
of the main surface of the resin seal member extends along a  
first side of the main surface of the semiconductor chip, the  
main surface of the resin seal member has a second side  
intersecting the first side thereof, the second side of the  
main surface of the resin seal member extending along a second  
side of the main surface of the semiconductor chip which  
second side intersects the first side of the chip main  
surface, and in a section orthogonal to the second side of  
the main surface of the semiconductor chip, a] A sectional  
area of an area between the main surface of the wiring  
substrate and the main surface of the resin seal member at a  
position outside a side face of the semiconductor chip is  
smaller than a sectional area of an area between the main

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surface of the semiconductor chip and the main surface of the resin seal member. [It is possible to suppress the occurrence of void.]

**MARKED UP VERSION OF REWRITTEN CLAIMS**

7. (Amended) A semiconductor device according to claim 4, wherein the main surface of the semiconductor chip is formed in a rectangular shape in which the first and second sides of the main surface of the semiconductor chip are a [short] long side and a [long] short side, respectively.

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